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(54) **SEMICONDUCTOR PACKAGE AND METHOD OF MANUFACTURING THE SAME**

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(57) **ABSTRACT**

A semiconductor package includes: a first redistribution layer; at least one lower die on the first redistribution layer; a first through-via on the first redistribution layer; a first molding material that molds the first redistribution layer, the at least one lower die, and the first through-via; a second redistribution layer on the at least one lower die, the first through-via, and the first molding material; at least one upper die on the second redistribution layer and having a thickness between 1.2 and 1.7 times, including endpoints, greater than a thickness of the at least one lower die; a second through-via on the second redistribution layer; a second molding material that molds the second redistribution layer, the at least one upper die, and the second through-via; and a heat dissipation member on the at least one upper die and the second through-via, wherein the heat dissipation member contacts the second through-via.

